

NTD32N06L

Power MOSFET 32 Amps, 60 Volts, Logic Level N-Channel DPAK

Designed for low voltage, high speed switching applications in power supplies, converters and power motor controls and bridge circuits.

Features

- Smaller Package than MTB30N06VL
- Lower $R_{DS(on)}$, $V_{DS(on)}$, and Total Gate Charge
- Lower and Tighter V_{SD}
- Lower Diode Reverse Recovery Time
- Lower Reverse Recovery Stored Charge

Typical Applications

- Power Supplies
- Converters
- Power Motor Controls
- Bridge Circuits

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	60	Vdc
Drain-to-Gate Voltage ($R_{GS} = 10\text{ M}\Omega$)	V_{DGR}	60	Vdc
Gate-to-Source Voltage	V_{GS}	± 20	Vdc
– Continuous	V_{GS}	± 30	
– Non-Repetitive ($t_p \leq 10\text{ ms}$)			
Drain Current	I_D	32	A dc
– Continuous @ $T_A = 25^\circ\text{C}$	I_D	22	
– Continuous @ $T_A = 100^\circ\text{C}$	I_{DM}	90	A pk
– Single Pulse ($t_p \leq 10\text{ }\mu\text{s}$)			
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	93.75 0.625	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 1)		2.88	W
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 2)		1.5	W
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to $+175$	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ (Note 3) ($V_{DD} = 50\text{ Vdc}$, $V_{GS} = 5\text{ Vdc}$, $L = 1.0\text{ mH}$, $I_{L(pk)} = 25\text{ A}$, $V_{DS} = 60\text{ Vdc}$, $R_G = 25\text{ }\Omega$)	E_{AS}	313	mJ
Thermal Resistance	$R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JA}$	1.6 52 100	$^\circ\text{C/W}$
– Junction-to-Case			
– Junction-to-Ambient (Note 1)			
– Junction-to-Ambient (Note 2)			
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

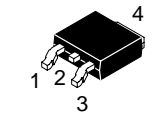
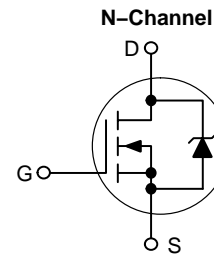
1. When surface mounted to FR4 board using 0.5" pad size.
2. When surface mounted to FR4 board using minimum recommended pad size.
3. Repetitive rating; pulse width limited by maximum junction temperature.



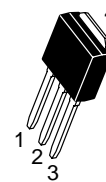
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V_{DSS}	$R_{DS(on)}$ TYP	I_D MAX
60 V	23.7 m Ω	32 A



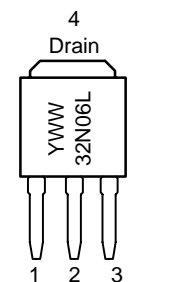
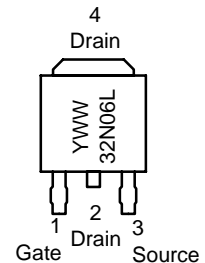
**DPAK
CASE 369C**
(Surface Mount)
Style 2



**DPAK
CASE 369D**
(Straight Lead)
Style 2

32N06L Device Code
Y = Year
WW = Work Week

MARKING DIAGRAMS



ORDERING INFORMATION

Device	Package	Shipping†
NTD32N06L	DPAK	75 Units/Rail
NTD32N06L-1	DPAK Straight Lead	75 Units/Rail
NTD32N06LT4	DPAK	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTD32N06L

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit	
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (Note 4) (V _{GS} = 0 Vdc, I _D = 250 μAdc) Temperature Coefficient (Positive)	V _{(BR)DSS}	60 -	70 62	- -	Vdc mV/°C	
Zero Gate Voltage Drain Current (V _{DS} = 60 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 60 Vdc, V _{GS} = 0 Vdc, T _J = 150°C)	I _{DSS}	- -	- -	1.0 10	μAdc	
Gate-Body Leakage Current (V _{GS} = ±20 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	-	-	±100	nAdc	
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage (Note 4) (V _{DS} = V _{GS} , I _D = 250 μAdc) Threshold Temperature Coefficient (Negative)	V _{GS(th)}	1.0 -	1.7 4.8	2.0 -	Vdc mV/°C	
Static Drain-to-Source On-Resistance (Note 4) (V _{GS} = 5 Vdc, I _D = 16 Adc)	R _{DS(on)}	-	23.7	28	mΩ	
Static Drain-to-Source On-Resistance (Note 4) (V _{GS} = 5 Vdc, I _D = 20 Adc) (V _{GS} = 5 Vdc, I _D = 32 Adc) (V _{GS} = 5 Vdc, I _D = 16 Adc, T _J = 150°C)	V _{DS(on)}	- - -	0.48 0.78 0.61	0.67 - -	Vdc	
Forward Transconductance (Note 4) (V _{DS} = 6 Vdc, I _D = 16 Adc)	g _{FS}	-	27	-	mhos	
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	-	1214	1700	pF
Output Capacitance		C _{oss}	-	343	480	
Transfer Capacitance		C _{rss}	-	87	180	
SWITCHING CHARACTERISTICS (Note 5)						
Turn-On Delay Time	(V _{DD} = 30 Vdc, I _D = 32 Adc, V _{GS} = 5 Vdc, R _G = 9.1 Ω) (Note 4)	t _{d(on)}	-	12.8	30	ns
Rise Time		t _r	-	221	450	
Turn-Off Delay Time		t _{d(off)}	-	37	80	
Fall Time		t _f	-	128	260	
Gate Charge	(V _{DS} = 48 Vdc, I _D = 32 Adc, V _{GS} = 5 Vdc) (Note 4)	Q _T	-	23	50	nC
		Q ₁	-	4.5	-	
		Q ₂	-	14	-	
SOURCE-DRAIN DIODE CHARACTERISTICS						
Forward On-Voltage	(I _S = 20 Adc, V _{GS} = 0 Vdc) (Note 4) (I _S = 32 Adc, V _{GS} = 0 Vdc) (Note 4) (I _S = 20 Adc, V _{GS} = 0 Vdc, T _J = 150°C)	V _{SD}	- - -	0.89 0.95 0.74	1.0 - -	Vdc
Reverse Recovery Time	(I _S = 32 Adc, V _{GS} = 0 Vdc, di _S /dt = 100 A/μs) (Note 4)	t _{rr}	-	56	-	ns
		t _a	-	31	-	
		t _b	-	25	-	
Reverse Recovery Stored Charge		Q _{RR}	-	0.093	-	μC

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

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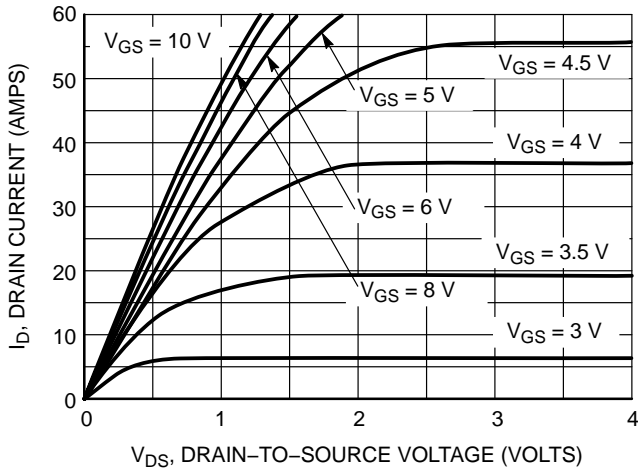


Figure 1. On-Region Characteristics

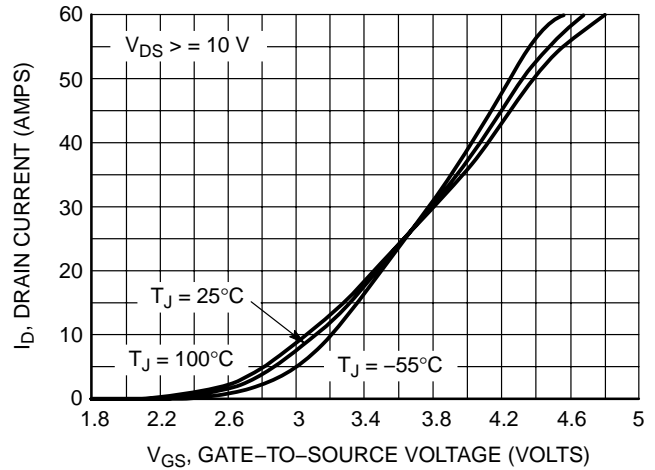


Figure 2. Transfer Characteristics

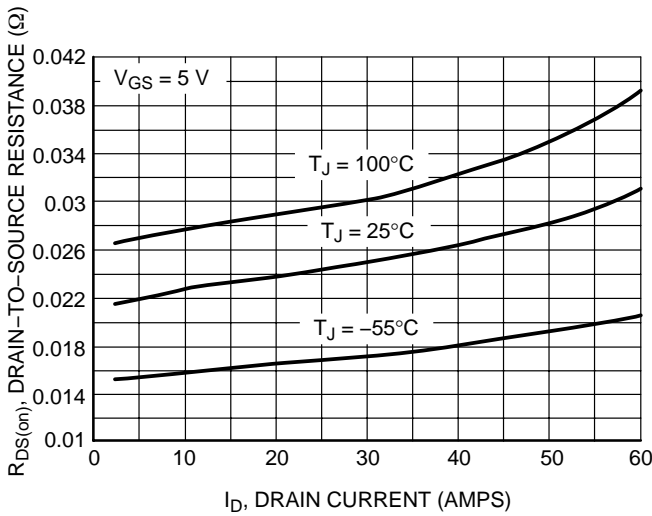


Figure 3. On-Resistance vs. Drain Current

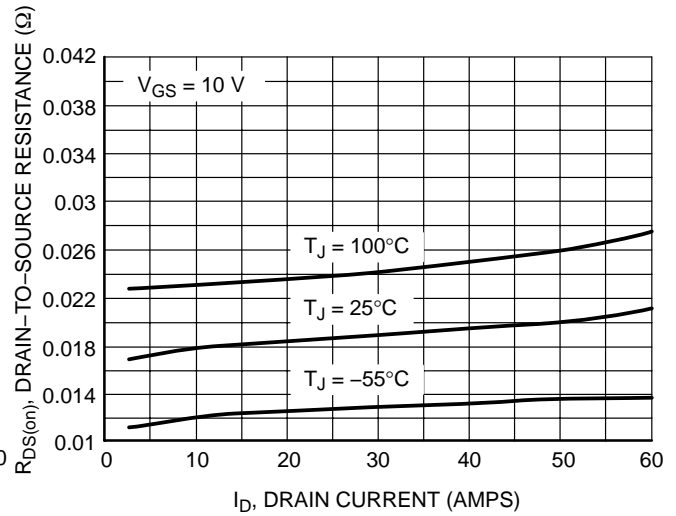


Figure 4. On-Resistance vs. Drain Current

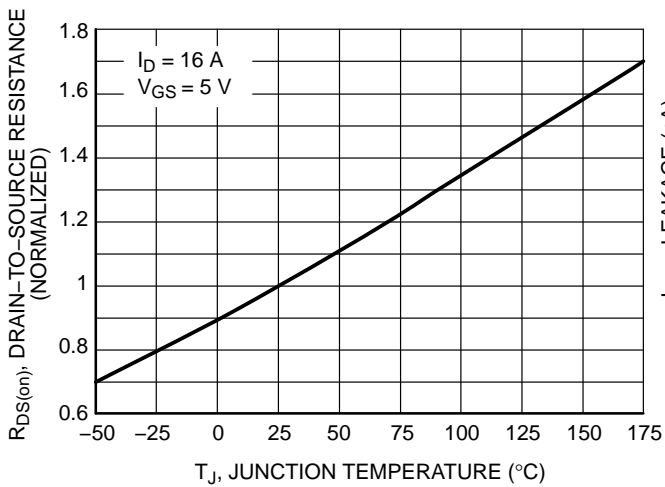


Figure 5. On-Resistance Variation with Temperature

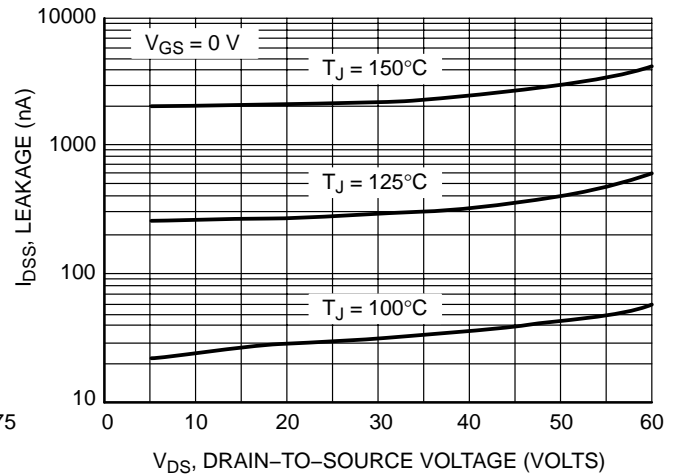


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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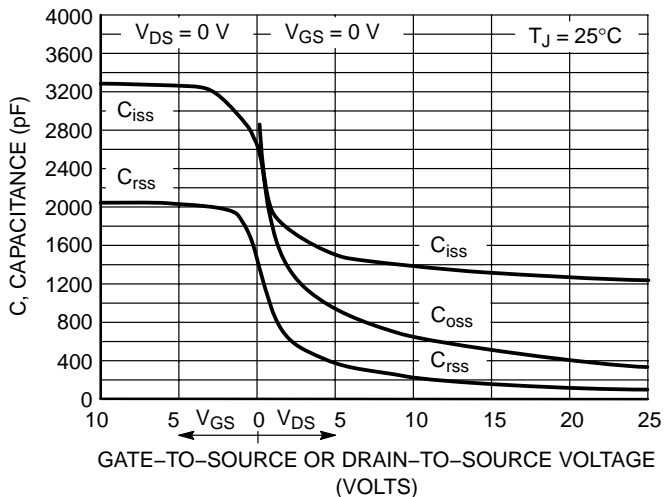


Figure 7. Capacitance Variation

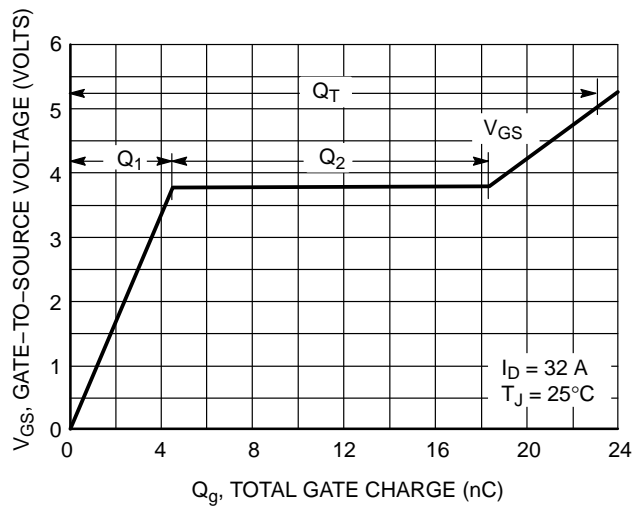


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

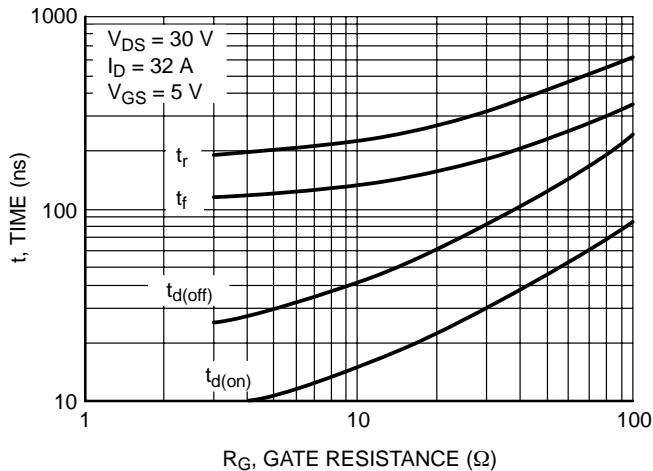


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

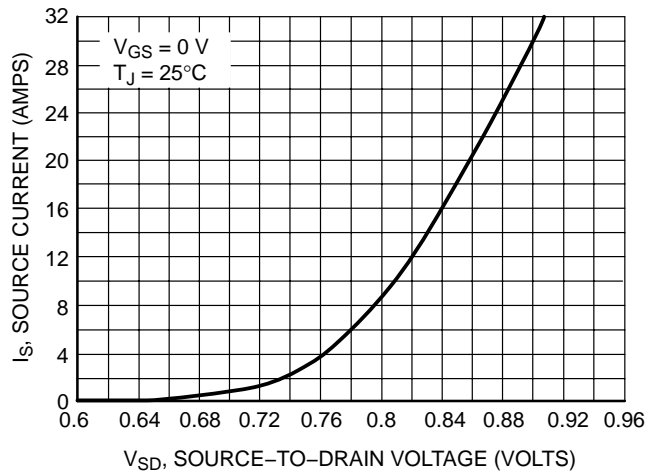


Figure 10. Diode Forward Voltage vs. Current

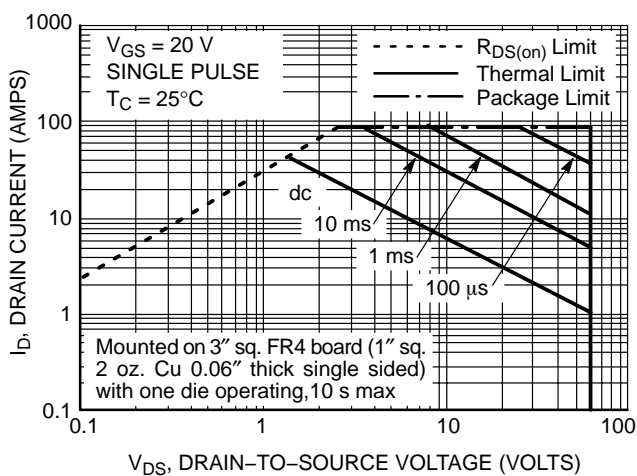


Figure 11. Maximum Rated Forward Biased Safe Operating Area

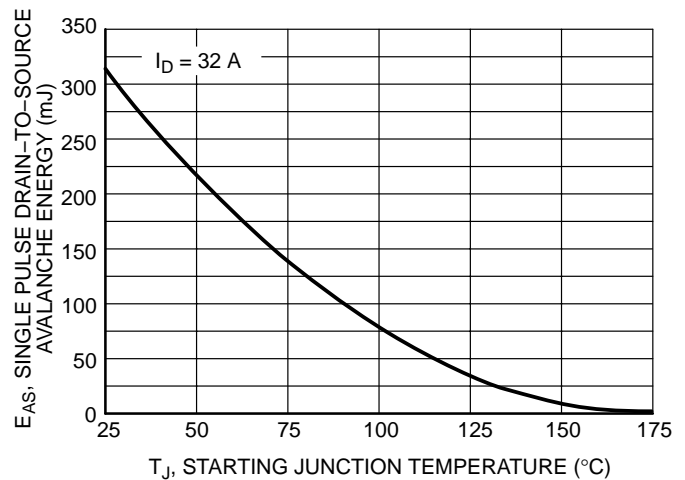


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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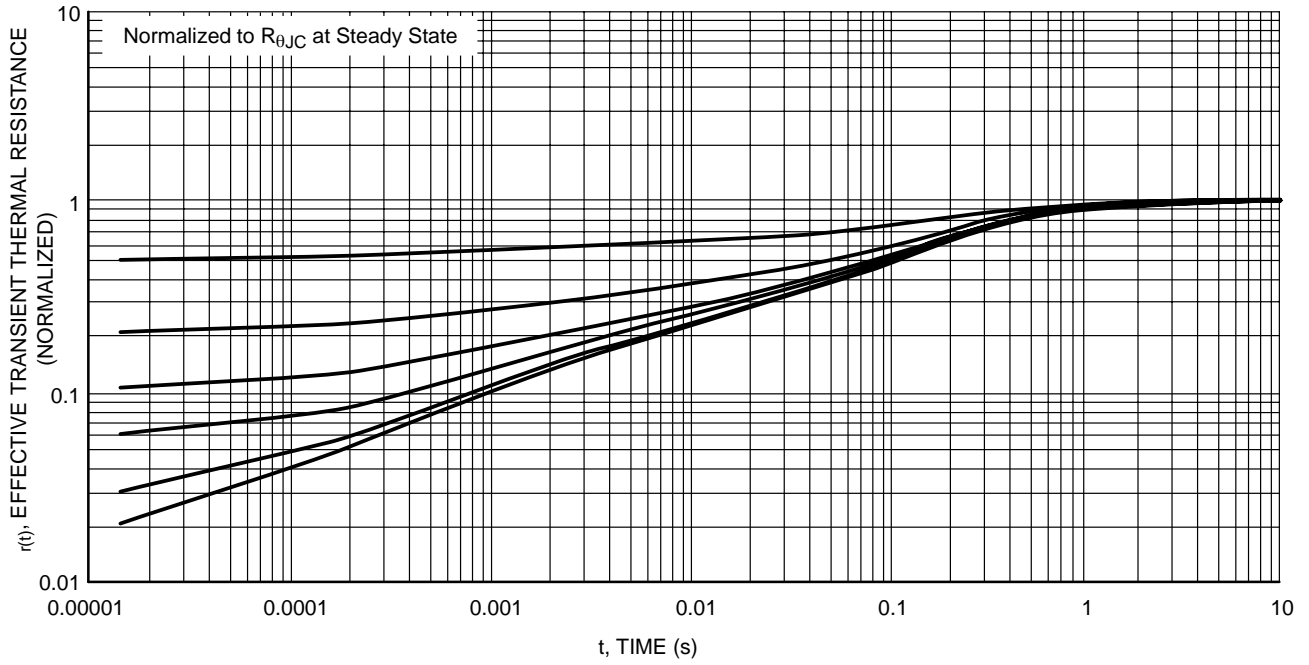


Figure 13. Thermal Response

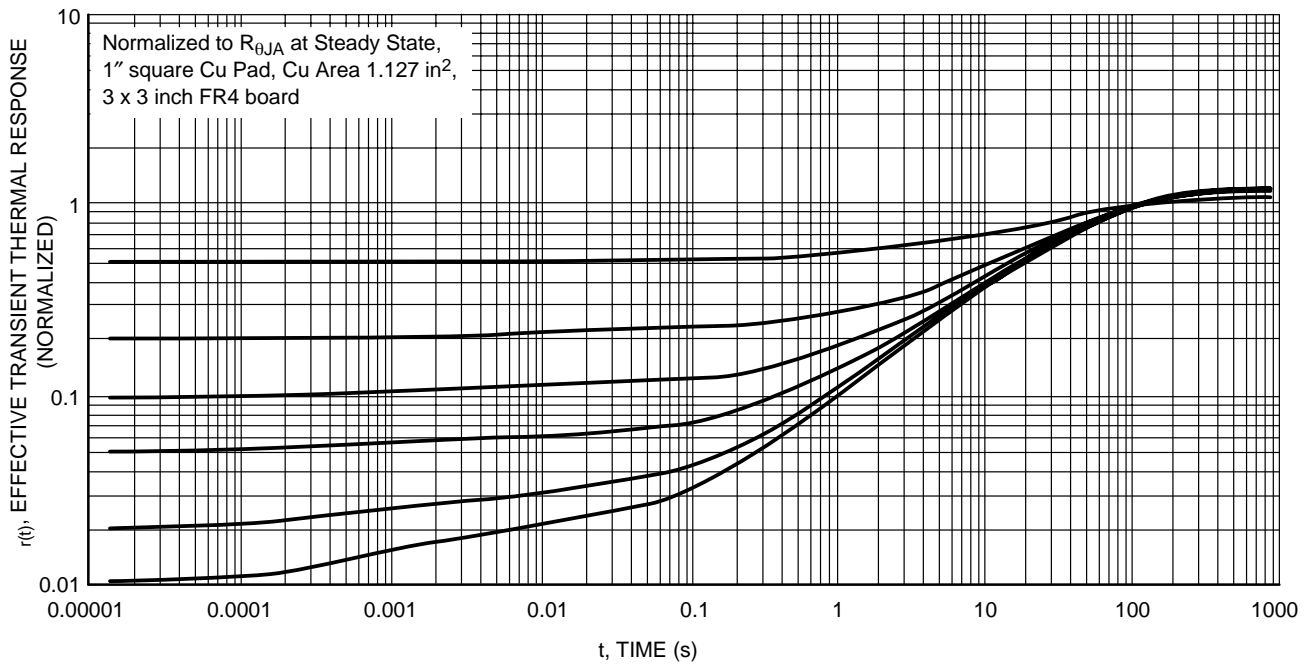
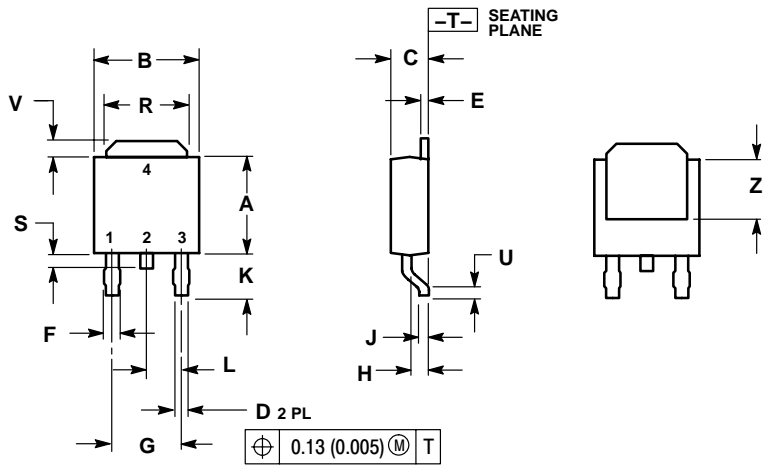


Figure 14. Thermal Response

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PACKAGE DIMENSIONS

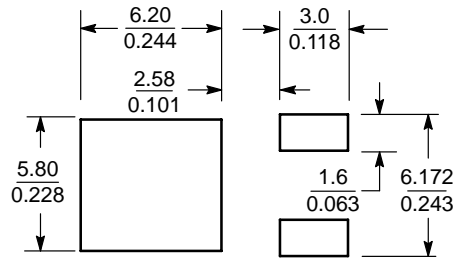
DPAK-3
CASE 369C-01
ISSUE O



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT

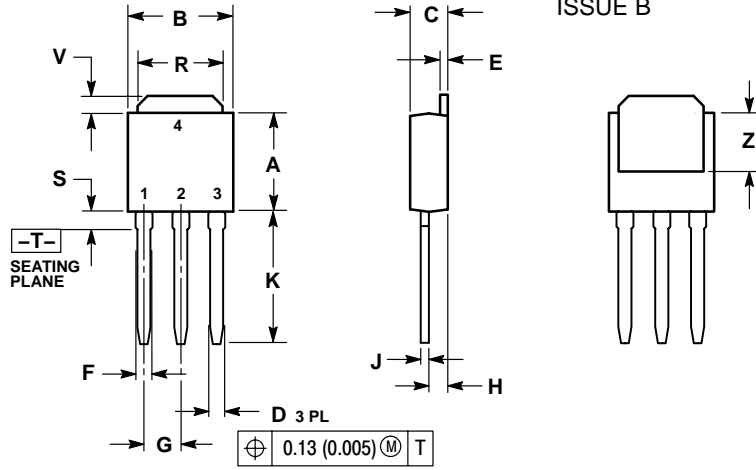


SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

NTD32N06L

PACKAGE DIMENSIONS

DPAK-3
CASE 369D-01
ISSUE B



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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